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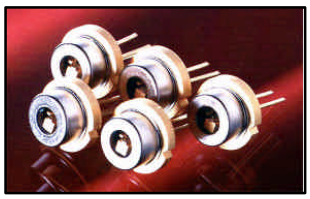


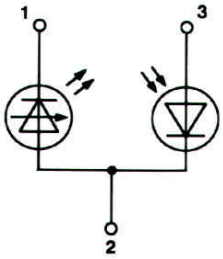
RLT6550G TECHNICAL DATA

High Power Visible Laserdiode

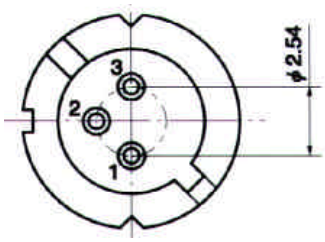
Structure: **High Efficiency MOVCD Quantum Well Design**
Lasing wavelength: **650 nm typ.**
Output power: **50 mW**
Package: **9 mm**

NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	60	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operating Temperature	T_C	-10 .. +40	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	cw operation		50		mW
Threshold Current	I_{th}	cw operation		80	130	mA
Operation Current	I_{op}	P_o = 50 mW		180	250	mA
Operation Voltage	V_{op}	P_o = 50 mW	2.0	2.2	2.5	V
Slope Efficiency	η	cw operation	0.4	0.7	1.0	W/A
Lasing Wavelength	λ	P_o = 50 mW		650	665	nm
Beam Divergence	$\theta_{//}$	P_o = 50 mW	5	7	14	°
Beam Divergence	$\theta_{\perp}$	P_o = 50 mW	30	38	40	°
Lasing Aperture	A	P_o = 50 mW		20x1		µm²
Monitor Current	I_m	P_o = 50 mW		0.5	2.0	mA